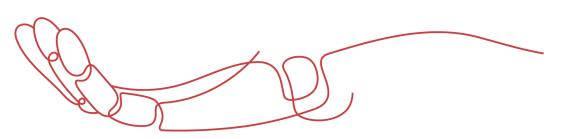




PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at







Datasheet

ources Samples

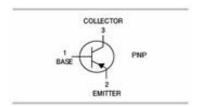
Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.



PNP Silicon Epitaxial Planar Transistor

FEATURES

- $P_{CM} = 0.5W (T_A = 25^{\circ}C)$
- High voltage
- Complementary: A42





APPLICATIONS

• Designed for high voltage driver appliication

SOT-89

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	-300	V	
V _{CEO}	Collector-Emitter Voltage	-300	V	
V _{EBO}	Emitter-Base Voltage	-5	V	
Ic	Collector Current -Continuous	-0.5	А	
Pc	Collector Dissipation	500	mW	
T_{j} , T_{stg}	Junction and Storage Temperature	-55 to +150	${\mathbb C}$	



ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μΑ,I _E =0	-300			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1.0mA,I _B =0	-300			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μΑ,I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-200V,I _B =0			-0.25	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-3V,I _C =0			-0.1	μA
		V _{CE} =-10V,I _C =-1mA	60			
DC current gain	h _{FE}	V _{CE} =-10V,I _C =-10mA	100	300		
		V _{CE} =-10V,I _C =-30mA	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-20mA, I _B =-2mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-20mA, I _B =-2mA			-0.9	V
Transition frequency	f⊤	V _{CE} =-20V, I _C =-10mA f=100MHz		50		MHz
Collector output capacitance	C _{ob}	V _{CB} =-20V,I _E =0,f=1MHz		6		pF



TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

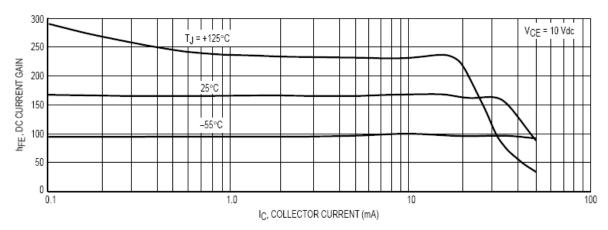


Figure 1. DC Current Gain

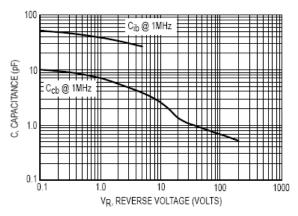


Figure 2. Capacitance

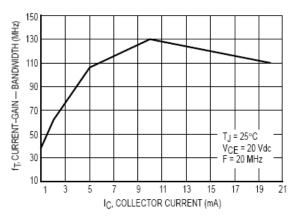


Figure 3. Current-Gain - Bandwidth

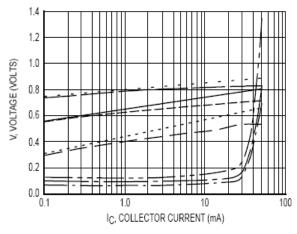
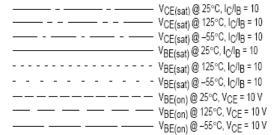


Figure 4. "ON" Voltages

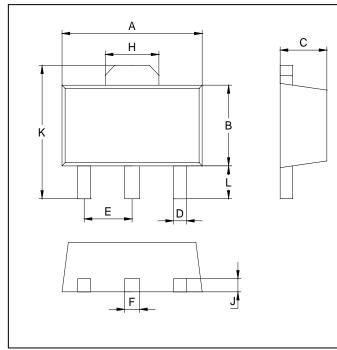




PACKAGE OUTLINE

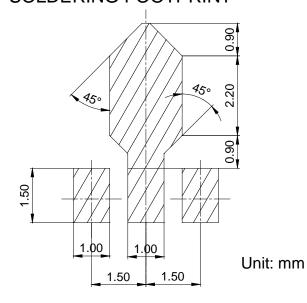
Plastic surface mounted package

SOT-89



SOT-89						
Dim	Min	Max				
Α	4.30	4.70				
В	2.25	2.65				
С	1.30	1.70				
D	0.30	0.50				
E	1.40	1.60				
F	0.38	0.58				
Н	1.60	1.80				
J	0.30	0.50				
L	0.90	1.10				
K	3.95	4.35				
All Dimensions in mm						

SOLDERING FOOTPRINT





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